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**AMENDMENTS TO THE CLAIMS**

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1. (previously amended) A non-volatile synchronous memory device comprising:  
an array of non-volatile memory cells arranged in a plurality of addressable  
banks, each bank comprises addressable rows and columns of non-volatile  
memory cells; and  
a plurality of bank buffers, the bank buffers and addressable banks coupled one to  
one, wherein each of the plurality of bank buffers is adapted to store data from  
a row of memory cells contained in its corresponding addressable bank of the  
plurality of addressable banks.
2. (original) The non-volatile synchronous memory device of claim 1 wherein the  
plurality of addressable banks comprise four addressable banks.
3. (original) The non-volatile synchronous memory device of claim 1 further  
comprising control circuitry to copy data from a first row of a first bank of the  
plurality of addressable banks to a first buffer of the plurality of buffers.
4. (original) The non-volatile synchronous memory device of claim 3 wherein an  
address of the first row is predefined and the control circuitry copies the data in  
response to an externally provided command.
5. (original) The non-volatile synchronous memory device of claim 1 wherein the  
plurality of buffers can be read while data is written to the plurality of banks.
6. (previously amended) A processing system comprising:  
a processor; and  
a non-volatile synchronous memory device coupled to the processor and  
comprising:

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an array of non-volatile memory cells arranged in a plurality of addressable banks, each bank comprises addressable rows and columns of non-volatile memory cells, and

a plurality of bank buffers, the bank buffers and addressable banks coupled one to one, wherein each of the plurality of bank buffers is adapted to store data from a row of memory cells contained in its corresponding addressable bank of the plurality of addressable banks.

7. (original) The processing system of claim 6 wherein the plurality of addressable banks comprise four addressable banks.
8. (original) The processing system of claim 6 wherein the non-volatile synchronous memory device further comprises control circuitry to copy data from a first row of a first bank of the plurality of addressable banks to a first buffer of the plurality of buffers.
9. (original) The processing system of claim 8 wherein an address of the first row is predefined and the control circuitry copies the data in response to an externally provided command.
10. (original) The processing system of claim 6 wherein the plurality of buffers can be read while data is written to the plurality of banks.
11. (previously amended) A method of writing to a flash memory comprising:  
copying first data stored in a row of a first non-volatile memory cell array bank to a first buffer circuit using control circuitry of the flash memory;  
copying second data stored in a row of a second non-volatile memory cell array bank to a second buffer circuit using the control circuitry;  
performing a write operation to write third data to the first array bank using a first external processor coupled to the flash memory;

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reading the first data from the first buffer circuit using the first external processor  
while performing the write operation; and  
reading the second data from the second array bank using a second external  
processor coupled to the flash memory while performing the write operation.

12. (original) The method of claim 11 further comprising:  
monitoring a status of the flash memory to determine when the write operation is  
completed.
13. (previously amended) The method of claim 12 wherein monitoring is performed  
by the first external processor in response to the first data read from the buffer  
circuit.
14. (previously amended) The method of claim 11 wherein copying the first data is  
initiated by the first external processor coupled to the flash memory.
15. (previously amended) The method of claim 11 wherein copying the first data and  
performing the write operation is initiated by the first external processor coupled  
to the flash memory.
- 16-27. (cancelled)
28. (new) The non-volatile synchronous memory device of claim 4, wherein the  
externally provided command is a write command.
29. (new) The processing system of claim 9, wherein the externally provided  
command is a write command.
30. (new) The processing system of claim 6, further comprising:  
a second processor coupled to the non-volatile synchronous memory device.

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31. (new) The processing system of claim 30, wherein the non-volatile synchronous memory device is adapted to allow the second process to read data from a second bank of the array while the processor writes data to a first bank.
  32. (new) The method of claim 14, wherein copying the first data is initiated by the first external processor coupled to the flash memory further comprises copying the first data is initiated by a write command from the first external processor coupled to the flash memory.
  33. (new) A flash memory device comprising:  
an array of flash memory cells arranged in a plurality of addressable banks, each bank comprises addressable rows and columns of flash memory cells; and  
a plurality of bank buffers, the bank buffers and addressable banks coupled one to one, wherein each of the plurality of bank buffers is adapted to store data from a row of memory cells contained in its corresponding addressable bank of the plurality of addressable banks.
  34. (new) The flash memory device of claim 33, wherein the plurality of addressable banks comprise four addressable banks.
  35. (new) The flash memory device of claim 33, further comprises control circuitry to copy data from a first row of a first bank of the plurality of addressable banks to a first buffer of the plurality of buffers.
  36. (new) The flash memory device of claim 35, wherein an address of the first row is predefined and the control circuitry copies the data in response to an externally provided command.

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37. (new) The flash memory device of claim 33, wherein the plurality of buffers can be read while data is written to the plurality of banks.
38. (new) The flash memory device of claim 33, wherein the externally provided command is a write command.